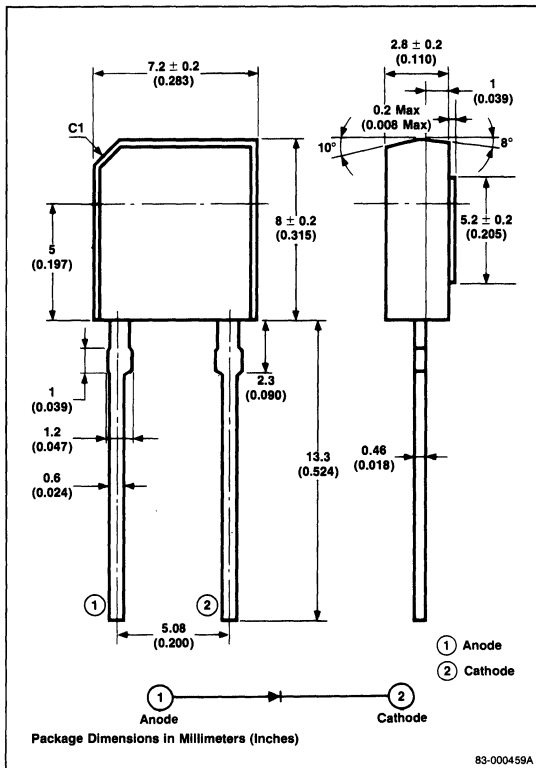


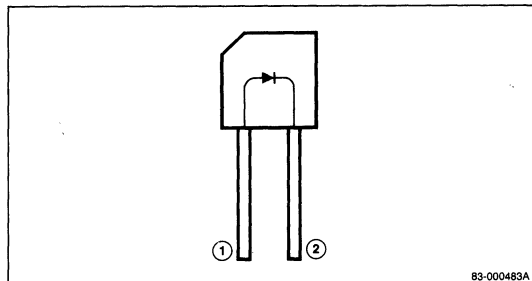
Description

The PH302 is a photo diode with a PIN structure. It has a wide photo-receiving area and high-speed response enabling applications for various types of remote control equipment. The resin material used for the package has the filter effect of transmitting only infrared.

Package Dimensions



Pin Connection



Features

- Ultrahigh-speed response ($t_r, t_f = 50\text{ns}$)
- The wavelength of maximum sensitivity matches that of an infrared LED ($\lambda_{S-MAX} = 940\text{nm}$)
- High sensitivity (50nA/lx)
- Wide dynamic range

Absolute Maximum Ratings

$T_A = +25^\circ\text{C}$

Reverse Voltage, V_R	32V
Power Dissipation, P_D	150mW
Junction Temperature, T_J	80°C
Storage Temperature, T_{STG}	-40°C to +80°C

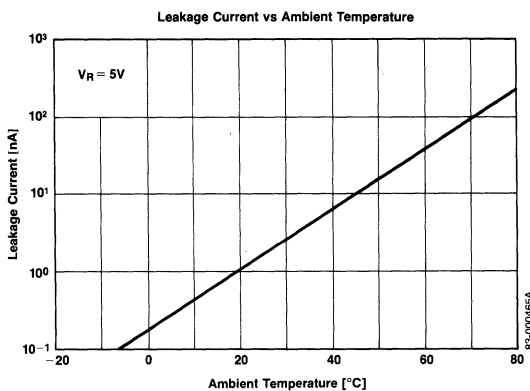
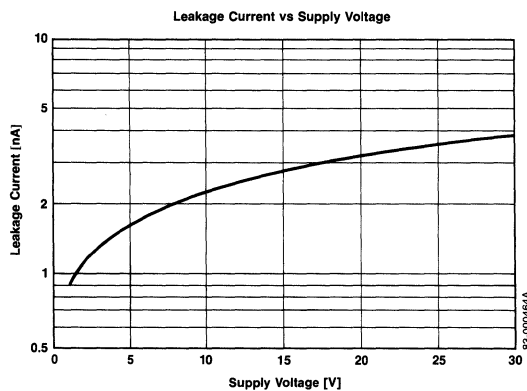
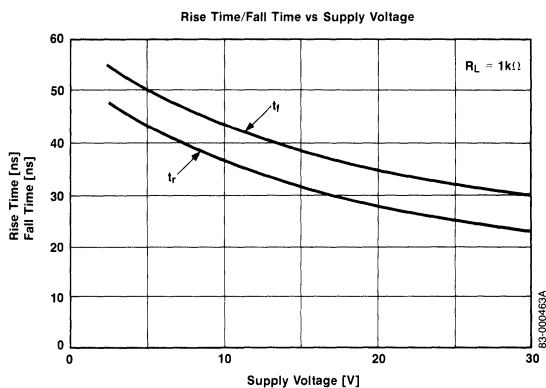
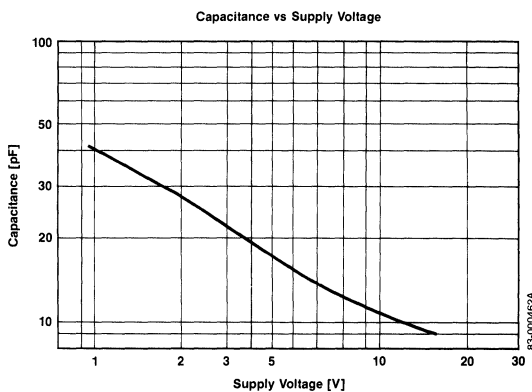
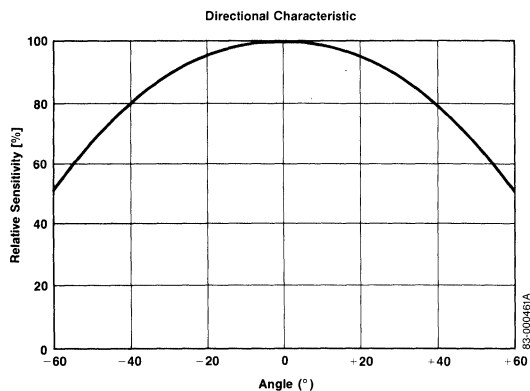
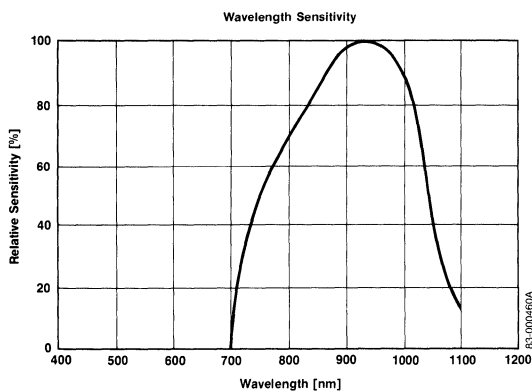
Electrical Characteristics

$T_A = +25^\circ\text{C}$

Parameters	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Dark Current	I_R			30	nA	$V_R = 10\text{V}$
Maximum Sensitivity Wavelength	λ_{MAX}		940		nm	
Quantum Efficiency	η		0.88			$\lambda = 940\text{nm}$
Spectral Sensitivity	S	35	50		nA/lx	$V_R = 5\text{V}$
Spectral Sensitivity	S		0.6		A/W	$\lambda = 940\text{nm}$
Open Circuit Voltage	V_L		285		mV	$E_V = 100\text{lx}$
Open Circuit Voltage	V_L		365		mV	$E_V = 1000\text{lx}$
Rise and Fall Time of the Photo Current from 10% to 90% and 90% to 10% of the Final Value	t_r, t_f		125		ns	$R_L = 1\text{k}\Omega$ $V_R = 0\text{V}$ $\lambda = 940\text{nm}$
	t_r, t_f		50		ns	$R_L = 1\text{k}\Omega$ $V_R = 5\text{V}$ $\lambda = 940\text{nm}$
Capacitance	C_T		14		pF	$V_R = 5\text{V}$ $f = 1\text{MHz}$
Radiant Sensitive Area	A		9		mm ²	
Noise Equivalent Power	NEP		4.2×10^{-14}		W/ $\sqrt{\text{Hz}}$	$V_R = 10\text{V}$
Detection Limit	D		6.6×10^{12}		cm/ $\sqrt{\text{Hz}\cdot\text{W}}$	

Typical Characteristics

$T_A = +25^\circ\text{C}$



Typical Characteristics (cont)

$T_A = +25^\circ\text{C}$

